

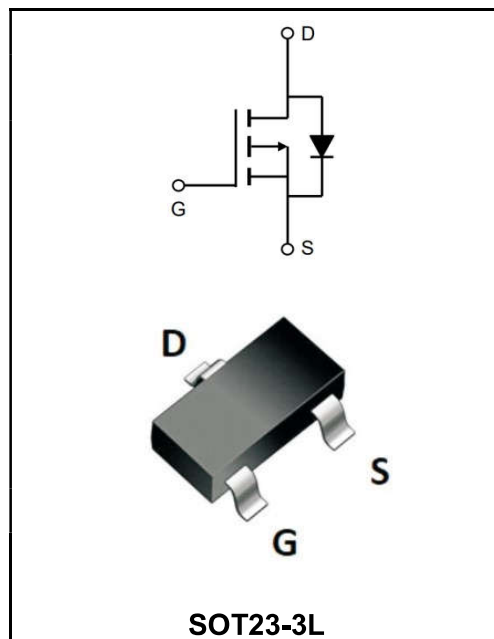
-100V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	-3A
V_{DSS}	-100V
$R_{DS(on)}-typ(@V_{GS}=-10V)$	< 350mΩ (Type: 260mΩ)

Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



Product Specification Classification

Part Number	Package	Marking	Pack
YFW3P10MI	SOT23-3L	3P10	3000PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-100	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current, $V_{GS} @ -10V^1$ @ $T_A=25^\circ C$	I_D	-3	A
Continuous Drain Current, $V_{GS} @ -10V^1$ @ $T_A=70^\circ C$	I_D	-1.7	A
Pulsed Drain Current ²	I_{DM}	-9	A
Total Power Dissipation ³ @ $T_A=25^\circ C$	P_D	1.5	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	125	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	80	°C/W

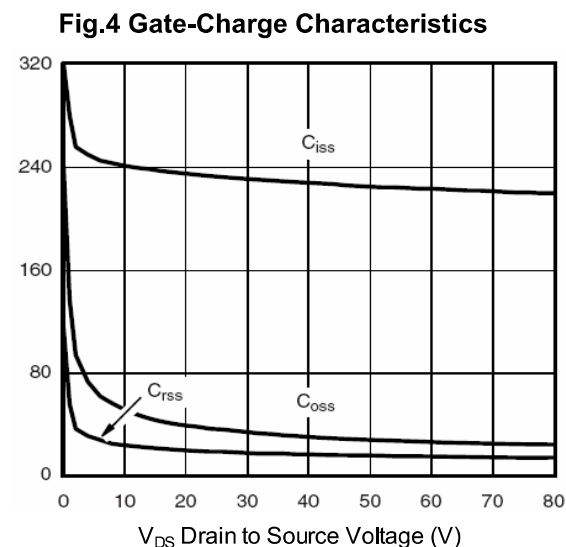
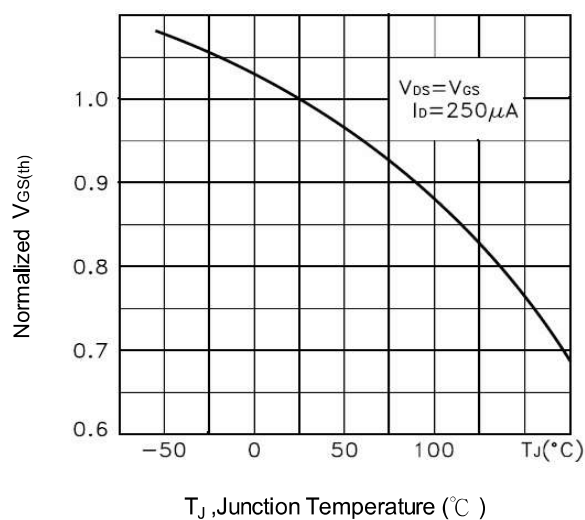
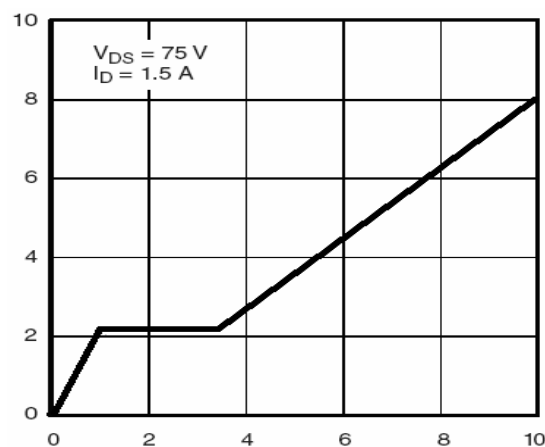
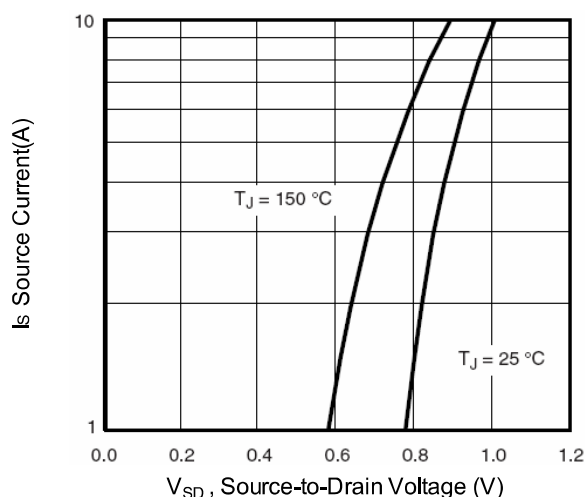
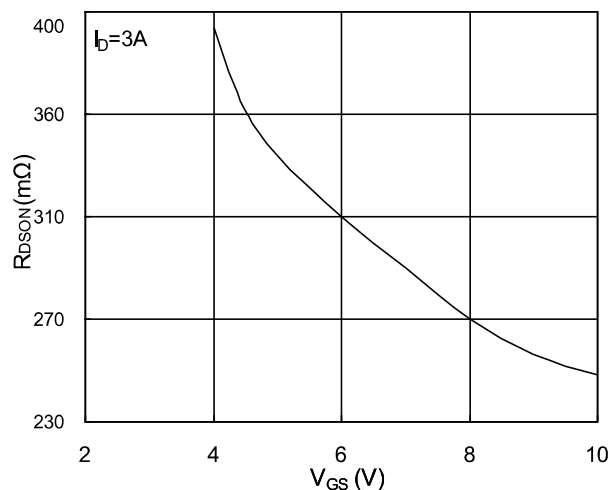
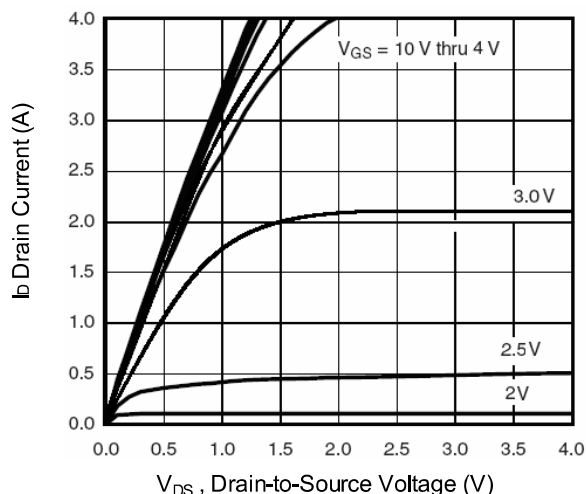
Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	BV_{DSS}	-100	-111	-	V
BVDSS Temperature Coefficient	Reference to 25°C, $I_D=-1mA$	$\Delta BV_{DSS}/\Delta T_J$	-	-0.0624	-	V/°C
Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-3A$	$R_{DS(ON)}$	-	260	350	mΩ
	$V_{GS}=-4.5V, I_D=-2A$		-	320	400	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	$V_{GS(th)}$	-1.2	-1.9	-2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	4.5	-	mV/°C
Drain -Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V, T_J=25^\circ C$	I_{DSS}	-	-	1	μA
	$V_{DS}=-100V, V_{GS}=0V, T_J=100^\circ C$		-	-	100	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Forward Transconductance	$V_{DS}=-5V, I_D=-0.8A$	g_{FS}	-	3	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g		16	32	Ω
Total Gate Charge(-4.5V)	$V_{DS}=-15V$ $V_{GS}=-4.5V$ $I_D=-0.5A$	Q_g	-	4.5	-	nC
Gate-Source Charge		Q_{gs}	-	1.14	-	
Gate-Drain Charge		Q_{gd}	-	1.5	-	
Turn-on delay time	$V_{DD}=-50V$ $V_{GS}=-10V$ $R_G=3.3\Omega$ $I_D=-0.5A$	$t_{d(on)}$	-	17.6	-	nS
Rise Time		T_r	-	2.7	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	4.5	-	
Fall Time		t_f	-	3	-	
Input Capacitance	$V_{DS}=-15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	550	-	pF
Output Capacitance		C_{oss}	-	56	-	
Reverse Transfer Capacitance		C_{rss}	-	35	-	
Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	I_S	-	-	-3	A
Pulsed Source Current ^{2,4}		I_{SM}	-	-	-9	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	V_{SD}	-	-	-1.3	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves



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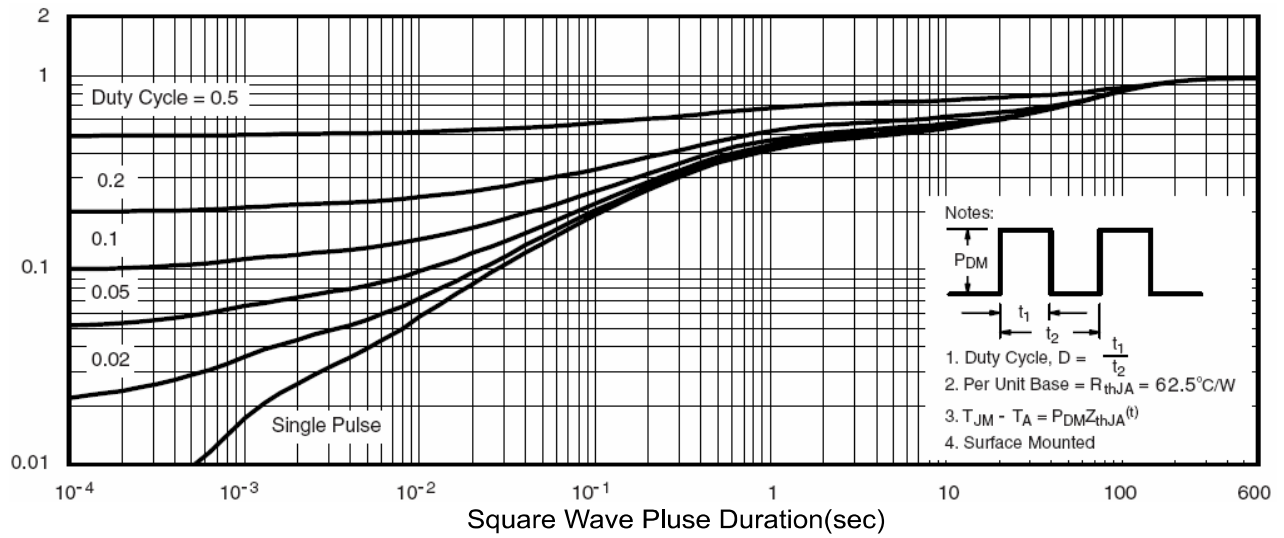


Fig.9 Normalized Maximum Transient Thermal Impedance

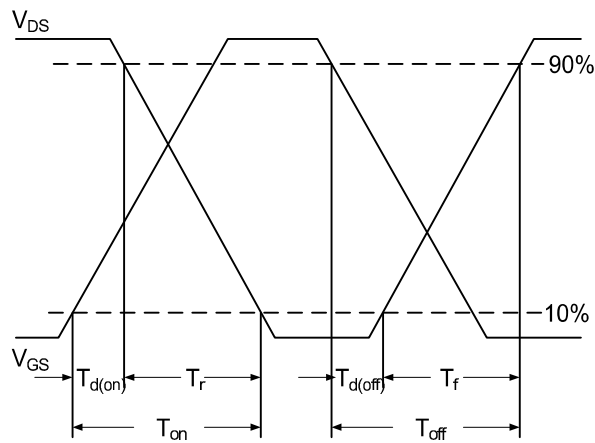


Fig.10 Switching Time Waveform

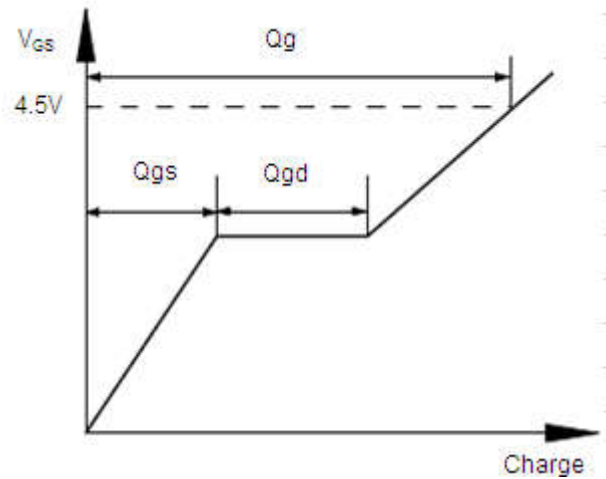
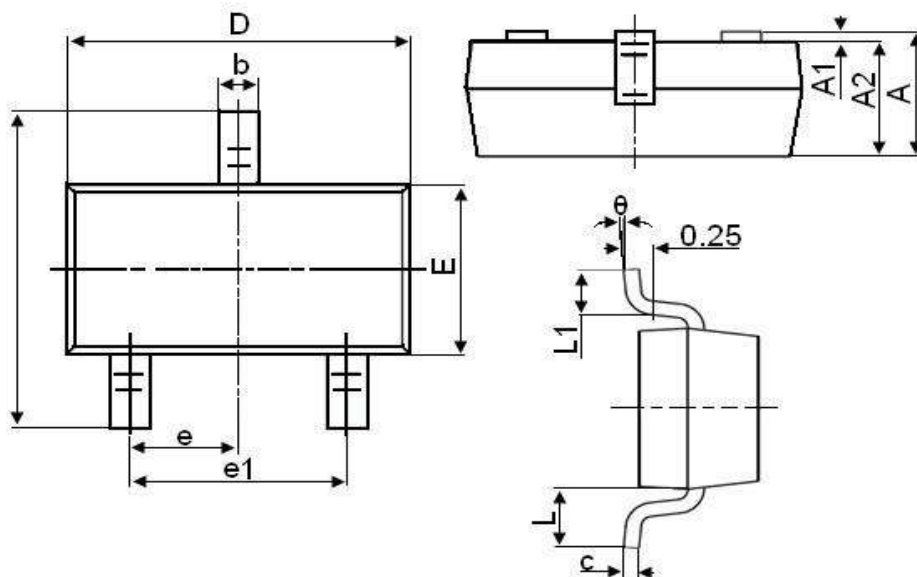


Fig.11 Gate Charge Waveform

SOT23-3L



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°